

Problems for Final Report (physics of semiconductors)

Shingo Katsumoto

Dept. Physics and Inst. for Solid State Physics, University of Tokyo

July 13, 2016

Problem1

Let us consider a pn -junction of Si at the temperature 300 K. In the p -layer the acceptor (boron, B) concentration is 10^{21} m^{-3} and in the n -layer the donor (phosphorous, P) concentration is 10^{20} m^{-3} . The doping profile is abrupt.

1. Obtain the built-in potential.
2. Calculate the depletion layer widths for p - and n -layers at reverse bias voltage -5 V .
3. Calculate the differential capacitance at reverse bias voltage -5 V for the area $1 \text{ mm} \times 1 \text{ mm}$.

Let put another p -layer and make a pn p transistor (gedankenexperiment). The hole diffusion length in the base is $10 \mu\text{m}$.

4. Calculate h_{FE} for base widths $0.5 \mu\text{m}$ and $0.1 \mu\text{m}$. (Ignore depletion layer widths, other non-ideal factors. Calculate under the simplest approximation.)

Problem2

Figure 1 (in the next page) shows the Shubnikov-de Haas oscillation and the quantum Hall effect in two-dimensional electrons.

1. Calculate the electron concentration from the low ($\leq 0.5 \text{ T}$) field data.
2. Something happened around 0.65 T . What is it?

Problem3

Consider a double barrier resonant diode with GaAs as the well material and $\text{Al}_{0.4}\text{Ga}_{0.6}\text{As}$ as the barrier material. Let us adopt $E_g=1.424 \text{ eV}$ for GaAs and $E_g=1.424+1.265x+0.265x^2 \text{ (eV)}$ for $\text{Al}_x\text{Ga}_{1-x}\text{As}$ and $\Delta E_c : \Delta E_v = 6:4$. The electron effective mass in GaAs is $0.067m_0$ and ignore the change in $\text{Al}_x\text{Ga}_{1-x}\text{As}$. Consider n -type electrodes (note that in the lecture we considered p -type).

1. Obtain the transfer matrix of 5 nm thickness $\text{GaAs-Al}_{0.4}\text{Ga}_{0.6}\text{As}$.
2. Calculate the transmission probability of resonant diode with two 5 nm barriers and a 5 nm well region as a function of incident energy (from 0 to the top of the barrier with an appropriate interval) and plot in a figure.

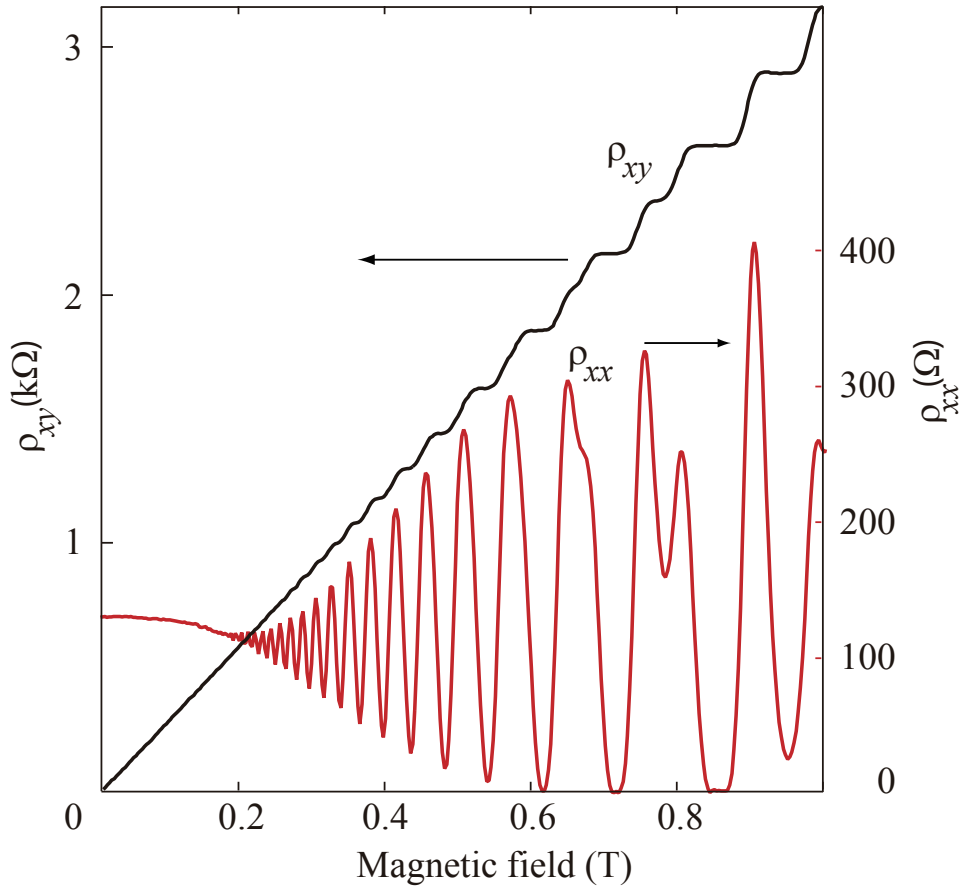
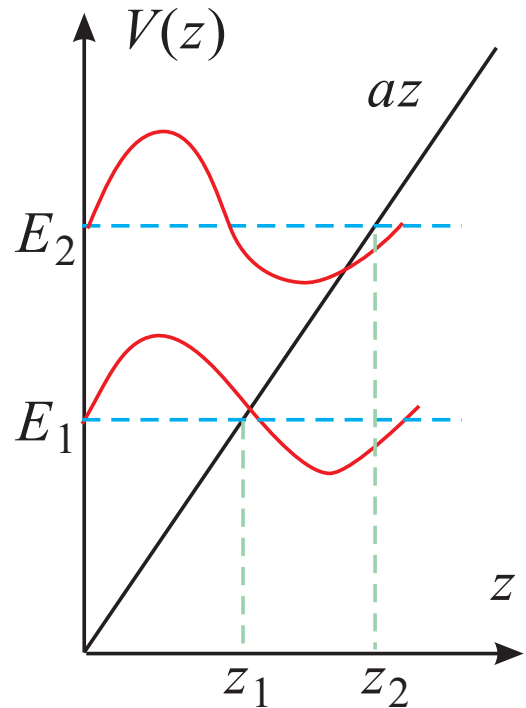


Figure 1: Shubnikov-de Haas oscillation of a two-dimensional electron system

Problem4

Let us consider the rectangular potential illustrate in the right.

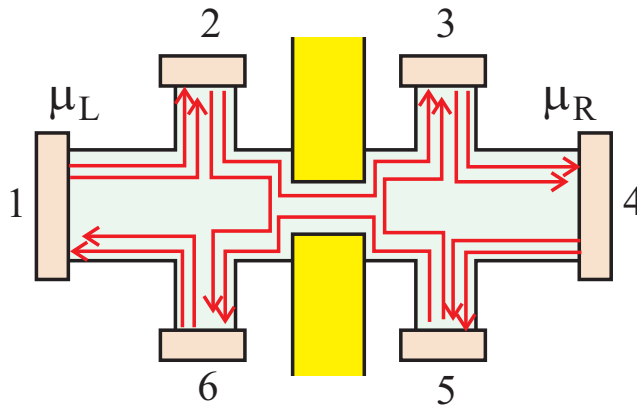
1. First consider the most coarse approximation. Choosing a kinetic energy E determines the effective potential with E/a . Now let us approximate the potential with a rectangular potential of width E/a , bottom $V(0)$, infinite barrier height. Let m^* be the effective mass and obtain the eigen energies from lower level with index $n = 1, 2, \dots$.
2. Compare the above result with more accurate one on Airy functions.
3. Also try comparison with Wenzel-Kramers-Brillouin (WKB) approximation for wavefunction penetration into the barrier.



Problem5

In the left figure the green region indicates 2DEG, 1 to 6 are the electric contacts, the yellow regions are metallic gates. The structure has a quantum point contact in the middle. In the integer quantum Hall state with filling factor ν , the sample has ν edge modes. With applying gate voltage, we can tune the number of modes which transmit through the QPC, to χ . Other modes are completely reflected by the QPC. The current is through 1 and 4.

1. Obtain the longitudinal resistance R_L , which is measured from the voltage between 2 and 3 V_{23} or 6 and 5 V_{65} .
2. Obtain the Hall resistance R_H , measured from V_{26} or V_{35} .



Problem6

Consider a 2DEG under IQHE with $\nu = 1$. The edge modes can bring finite current without energy dissipation and the resistance is zero. The conductance of one-dimensional edge mode is then the inverse of the resistance and infinity. Let write the quantum resistance h/e^2 as R_q .

Two dimensional resistivity tensor is written as

$$\rho = \begin{pmatrix} 0 & R_q \\ -R_q & 0 \end{pmatrix}.$$

Then the two dimensional conductivity tensor defined by the inverse of resistivity tensor is

$$\sigma = \rho^{-1} = \frac{1}{R_q^2} \begin{pmatrix} 0 & -R_q \\ R_q & 0 \end{pmatrix}.$$

That is, $\sigma_{xx}=0$! Does the calculation contain an error? If it does, what is the error? Or can you solve the puzzle?